

PRELIMINARY AMENDMENT

Prior to the substantive examination of the above-identified application, please amend the application as follows:

IN THE CLAIMS:

1-6. (Cancelled).

7. (Original) A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using CMP,

wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a tube which substantially does not contain fine particles for reinforcing the strength of the tube is used as a tube for supplying the slurry.

8. (Original) The polishing method of claim 7, wherein the tube is a vinyl chloride type tube or a silicon rubber type tube.

9. (Original) A method for fabricating a semiconductor device, comprising the polishing method of any one of claims 1 through 8.

10. (Original) A system for polishing a substrate using CMP, comprising:

a CMP apparatus for polishing the substrate; and
a tube-type slurry supply pump for supplying a slurry during polishing,
wherein a tube for the tube-type slurry supply pump is a tube in which at least the
inner surface is formed of a vinyl chloride material.

11-14. (Cancelled)

15. (New) A device formation method comprising of,
placing a substrate in a CMP unit,
supplying a slurry on the substrate through a tube connected to a slurry pump,
polishing the substrate on which the slurry is supplied, and
wherein the tube substantially does not contain fine particles for reinforcing the
strength of the tube.

16. (New) The device formation method of claim 15, wherein the tube is a
vinyl chloride type tube or a silicon rubber type tube.

17. (New) The polishing method of claim 15, wherein the tube has at least an
inner surface formed of a vinyl chloride material.

18. (New) A device formation method comprising of,
placing a substrate in a CMP unit,
supplying a slurry on the substrate through a tube connected to a slurry pump,

polishing the substrate on which the slurry is supplied, and
wherein the tube is a vinyl chloride type tube.

19. (New) A system for forming a semiconductor device comprising:
a CMP unit for polishing a substrate;
a slurry pump for supplying a slurry to the CMP unit;
a tube connected between the CMP unit and the slurry pump, and
wherein the tube substantially does not contain fine particles for reinforcing the
strength of the tube.

20. (New) The system of claim 19, wherein the tube is a vinyl chloride type
tube or a silicon rubber type tube.

21. (New) A system for forming a semiconductor device comprising:
a CMP unit for polishing a substrate;
a slurry pump for supplying a slurry to the CMP unit;
a tube connected between the CMP unit and the slurry pump, and
wherein the tube has at least an inner surface formed of a vinyl chloride material.